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(54) **Title: CONTACT WRAP AROUND STRUCTURE**

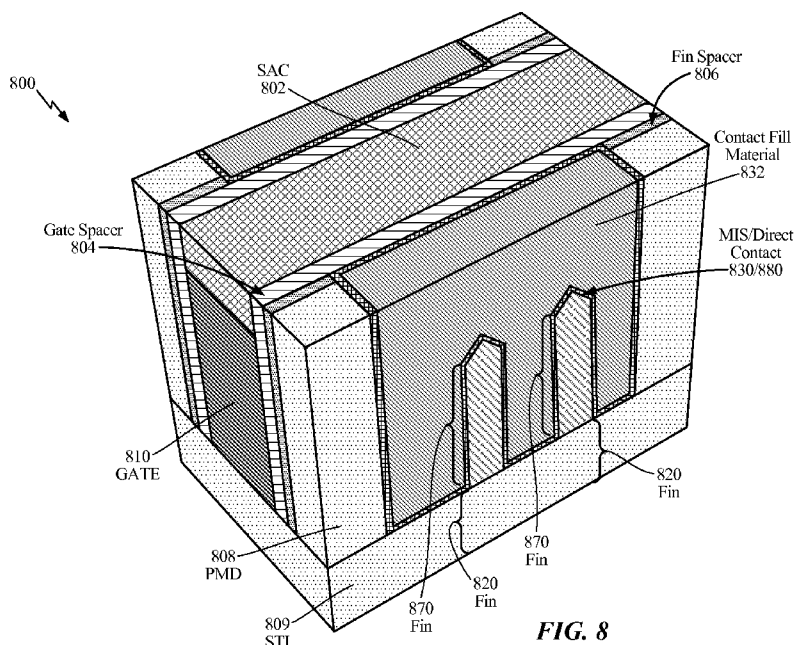


FIG. 8

(57) **Abstract:** A semiconductor device includes a gate stack. The semiconductor device also includes a wrap-around contact arranged around and contacting substantially all surface area of a regrown source/drain region of the semiconductor device proximate to the gate stack.



SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

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